

MAGNETIC TUNNELING JUNCTION ANTIFUSE DEVICE

Abstract of the Disclosure

An MRAM device having a plurality of MRAM cells formed of a fixed magnetic layer, a second soft magnetic layer and a dielectric layer interposed between the fixed magnetic layer and the soft magnetic layer. The MRAM cells are all formed simultaneously and at least some of the MRAM cells are designed to function as antifuse devices whereby the application of a selected electrical potential can short the antifuse device to thereby affect the functionality of the MRAM device.

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